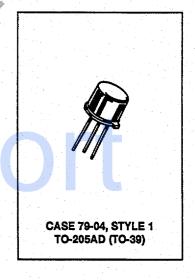
2N2219AJAN, JTX, JTXV, JANS Processed per MIL-S-19500/251 NPN Silicon Small-Signal Transistors

...designed for general-purpose switching and amplifier applications.



MAXIMUM RATINGS			
Rating	Symbol	Value	Unit
Collector-Emitter Voltage	VCEO	50	Vdc
Collector-Base Voltage	VCBO	75	Vdc
Emitter-Base Voltage	VEBO	6.0	Vdc
Collector Current	lc 🗼	800	mAde
Device Dissipation @ T _A = 25°C Derate above 25°C @ T _C = 25°C Derate above 25°C	Po	0.8 4.6 3.0 17	Watts mW/°C Watts mW/°C
Operating Junction and Storage Temperature Range	TJ, T _{stg}	- 65 to 200	



ELECTRICAL CHARACTERISTICS (TA = 25°C unless otherwis	se noted.)			
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage ⁽¹⁾ (IC = 10 mAdc, IE = 0)	V(BR)CEO	50	_	Vdc
Collector-Base Breakdown Voltage (IC = 10 μAdo, IE = 0)	V(BR)CBO	75		Vdc
Emitter-Base Breakdown Voltage (IE = 10 μAdc)	V(BR)EBO	6.0	_	Vdc
Collector Cutoff Current (VCB = 50 Vdc)	ICES	<u>-</u>	0.01	μAdc

(1) Pulsed. Pulse Width 250 to 350 µs, Duty Cycle 1.0 to 2.0%.

(continued)

2N2219A

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS (continued)				
Collector Cutoff Current (VCB = 60 Vdc) @ TA = 150°C (VCB = 60 Vdc)	ICBO	<u> </u>	0.01	μAdc
Emitter Cutoff Current (VEB = 4.0 Vdc, IC = 0)	IEBO	<u> </u>	0.01	μAdc
ON CHARACTERISTICS		*.)
DC Current Gain ⁽¹⁾ (IC = 0.1 mAde, V _{CE} = 10 Vdc)	hFE	50		
(I _C = 1.0 mAdc, V _{CE} = 10 Vdc)		75	325	
(IC = 10 mAdc, VCE = 10 Vdc)	7	100	_	
(I _C = 150 mAdc, V _{CE} = 10 Vdc)		100	300	
(IC = 500 mAde, VCE = 10 Vde)(1)		30	_	
$(I_C = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, T_A = -55^{\circ}C)$		35		
Collector-Emitter Saturation Voltage(1) (IC = 150 mAdc, IB = 15 mAdc)	V _{CE(sat)}		0.3	Vdc
(IC = 500 mAdc, IB = 50 mAdc)		_	1.0	
Base-Emitter Saturation Voltage(1) $(I_C = 150 \text{ mAdc}, I_B = 15 \text{ mAdc})$	VBE(sat)	0.6	1.2	Vdc
(I _C = 500 mAdc, I _B = 50 mAdc)		_	2.0	
SMALL-SIGNAL CHARACTERISTICS				
Output Capacitance (V _{CB} = 10 Vdc, f = 0.1 to 1.0 MHz)	Cobo		8.0	pF
Input Capacitance (VEB = 0.5 Vdc, f = 0.1 to 1.0 MHz)	C _{ibo}		25	pF
Current Gain (IC = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{fe}	75		_
Small–Signal Current Transfer Ratio, Magnitude (IC = 20 mAdc, VCE = 20 Vdc, f = 100 MHz)	Ihfel	2.5	12	_
SWITCHING CHARACTERISTICS (See Figure 4) (VCC = 30 Vdc, IC = 150 mAdc, IB = 15 mAdc)				
Turn-On Time	t _(on)		35	ns
Turn-Off Time	t(off)	-	300	ns

⁽¹⁾ Pulsed. Pulse Width 250 to 350 µs, Duty Cycle 1.0 to 2.0%.

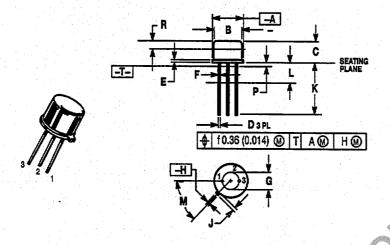
(continued)

2N2219A

Characteristics Tested Symbol Min Max	Unit
Collector Cutoff Current (VCB = 60 Vdc) - 10	nAdc

Delta from Pre-Burn-In Measured Values		Min	Max	
Delta Collector Cutoff Current	ΔICBO		±100 or ±5.0 whichever is greater	% of Initial Val nAdc
Delta DC Current Gain(1)	ΔhFE		±15	% of Initial Val
(1) Pulsed. Pulse Width 250 to 350 μs, Duty Cycle 1.0 to 2.09	%.			
이번 등 경쟁, 등고 있음 살인데 본 나라				
이 사고 그들은 시간에는 그 시티가 되었다고요?				
그리아 아침아는 그는 말을 보냈다면요?				
그는데요 어느 나는 얼마나 모양하는 나를 하셨다.				
		erita en la transita. La companya de la co		
물로 하는 물 맛이 말을 통해를 만들고 하셨다.				

PACKAGE DIMENSIONS



- 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION J MEASURED FROM DIMENSION
- 3. DIMENSION J. MEASURED FROM DIMENSION A MAXIMUM.
 4. DIMENSION B SHALL NOT VARY MORE THAN 0.25 (0.010) IN ZONE R. THIS ZONE CONTROLLED FOR AUTOMATIC HANDLING.
 5. DIMENSION F APPLIES BETWEEN DIMENSION P AND L. DIMENSION D APPLIES BETWEEN DIMENSION L AND K MINIMUM. LEAD DIAMETER IS UNCONTROLLED IN DIMENSION P AND BEYOND DIMENSION K MINIMUM.

STYLE 1: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 3: PIN 1. CATHODE 2. GATE 3. ANODE	STYLE 6: PIN 1. SOURCE 2. GATE 3. DRAIN (CASE)	STYLE9: PIN 1. SOURCE 2. DRAIN 3. GATE
STYLE 2:	STYLE 4:	PIN 1. DRAIN	STYLE 10:
PIN 1. DRAIN	PIN 1. MAIN TERM		PIN 1. COLLECTOR
2. SOURCE	2. GATE		2. EMITTER
3. GATE	3. MAIN TERM		3. BASE
	STYLE 5:	STYLE 8:	STYLE 11:
	PIN 1. COLLECTOR	PIN 1. ANODE	PIN 1. ANODE
	2. BASE	2. ANODE	2. OPEN
	3. EMITTER	3. CATHODE	3. CATHODE

	MILLIMETERS		INC	HES	
DIM	MIN	MAX	MIN	MAX	
A	8.51	9.39	0.335	0.370	
8	7.75	8.50	0.305	0.335	
C	6.10	6.60	0.240	0.260	
۵	0.41	0.53	0.016	0.021	
E	0.23	1.04	0.009	0.041	
F	0.41	0.48	0.016	0.019	
G	5.08	BSC	0.200	BSC	
H	0.72	0.86	0.028	0.034	
7	0.74	1.14	0.029	0.045	
_ K	12.70	19.05	0.500	0.750	
L	6.35		0.250	_	
M	45°	BSC	45°	BSC	
P	1	1.27	•	0.050	
R	2.54	-	0.100	-	

CASE 79-04 TO-205AD (TO-39)

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